

Electronic Supplementary Information for

**Twisted MoS₂/MX₂ heterobilayers: Effect of van der Waals interaction
on the electronic structure**

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Table S1. Computed lattice constant (in Å) and layer distance d (in Å) of the MX₂/MoS₂ heterobilayers.

	0°	13.2°	21.8°	27.8°	32.2°	38.2°	46.8°	60°
System	T	$\sqrt{19}$	$\sqrt{7}$	$\sqrt{13}$	$\sqrt{13}$	$\sqrt{7}$	$\sqrt{19}$	C7
CrSe₂	3.21	13.97	8.48	11.55	11.55	8.47	13.97	3.21
CrSe_{2-d}	3.14	3.41	3.41	3.44	3.44	3.44	3.41	3.16
MoSe₂	3.26	14.19	8.62	11.74	11.74	8.62	14.19	3.26
MoSe_{2-d}	3.11	3.41	3.41	3.40	3.41	3.41	3.42	3.12
WSe₂	3.26	14.20	8.62	11.75	11.75	8.62	14.20	3.26
WSe_{2-d}	3.11	3.41	3.41	3.41	3.41	3.41	3.41	3.11
WS₂	3.19	13.91	8.44	11.50	11.50	8.44	13.91	3.19
WS_{2-d}	3.10	3.34	3.38	3.35	3.37	3.37	3.37	3.10
CrS₂	3.13	13.65	8.28	11.28	11.28	8.28	13.64	3.13
CrS_{2-d}	3.10	3.35	3.36	3.35	3.36	3.36	3.36	3.18

Table S2. Computed direct bandgap E_{g1} (K-K, in eV) and indirect bandgap E_{g2} (Γ -K, in eV) of the MX₂/MoS₂ heterobilayers.

	0°	13.2°	21.8°	27.8°	32.2°	38.2°	46.8°	60°
CrSe ₂ -E _{g1}	0.76	0.76	0.76	0.77	0.77	0.77	0.76	0.76

CrSe₂_E_{g2}	0.65	0.79	0.79	0.80	0.81	0.82	0.79	0.69
CrSe₂_E_{g1_soc}	0.68	0.69	0.69	0.69	0.69	0.69	0.69	0.69
CrSe₂_E_{g2_soc}	0.62	0.76	0.76	0.77	0.77	0.78	0.76	0.66
MoSe₂_E_{g1}	0.80	0.74	0.73	0.74	0.74	0.73	0.74	0.75
MoSe₂_E_{g2}	0.75	0.88	0.87	0.87	0.88	0.86	0.89	0.74
MoSe₂_E_{g1_soc}	0.67	0.61	0.60	0.61	0.60	0.60	0.61	0.62
MoSe₂_E_{g2_soc}	0.76	0.88	0.86	0.86	0.86	0.86	0.88	0.74
WSe₂_E_{g1}	0.62	0.55	0.54	0.54	0.54	0.54	0.55	0.57
WSe₂_E_{g1}	0.69	0.79	0.79	0.78	0.78	0.79	0.79	0.67
WSe₂_E_{g1_soc}	0.34	0.27	0.26	0.26	0.26	0.26	0.27	0.30
WSe₂_E_{g2_soc}	0.66	0.72	0.73	0.71	0.71	0.73	0.72	0.64
WS₂_E_{g1}	1.53	1.46	1.47	1.47	1.47	1.47	1.46	1.47
WS₂_E_{g2}	1.18	1.22	1.26	1.23	1.24	1.24	1.24	1.16
WS₂_E_{g1_soc}	1.27	1.21	1.21	1.21	1.21	1.21	1.21	1.22
WS₂_E_{g2_soc}	1.18	1.22	1.25	1.23	1.24	1.24	1.23	1.16
CrS₂_E_{g1}	0.61	0.62	0.66	0.67	0.67	0.66	0.63	0.64
CrS₂_E_{g2}	0.33	0.43	0.44	0.44	0.45	0.44	0.44	0.39
CrS₂_E_{g1_soc}	0.44	0.49	0.47	0.50	0.50	0.49	0.50	0.50
CrS₂_E_{g2_soc}	0.31	0.41	0.41	0.42	0.43	0.42	0.42	0.37

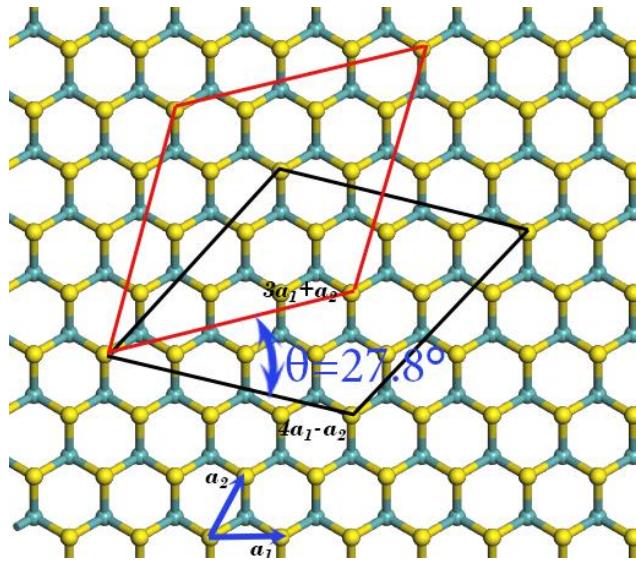


Figure S1. A schematic plot of the skewed supercell in a hexagonal lattice. The basis vector is $(n\mathbf{a}_1+m\mathbf{a}_2)$. The rotation angle is θ .

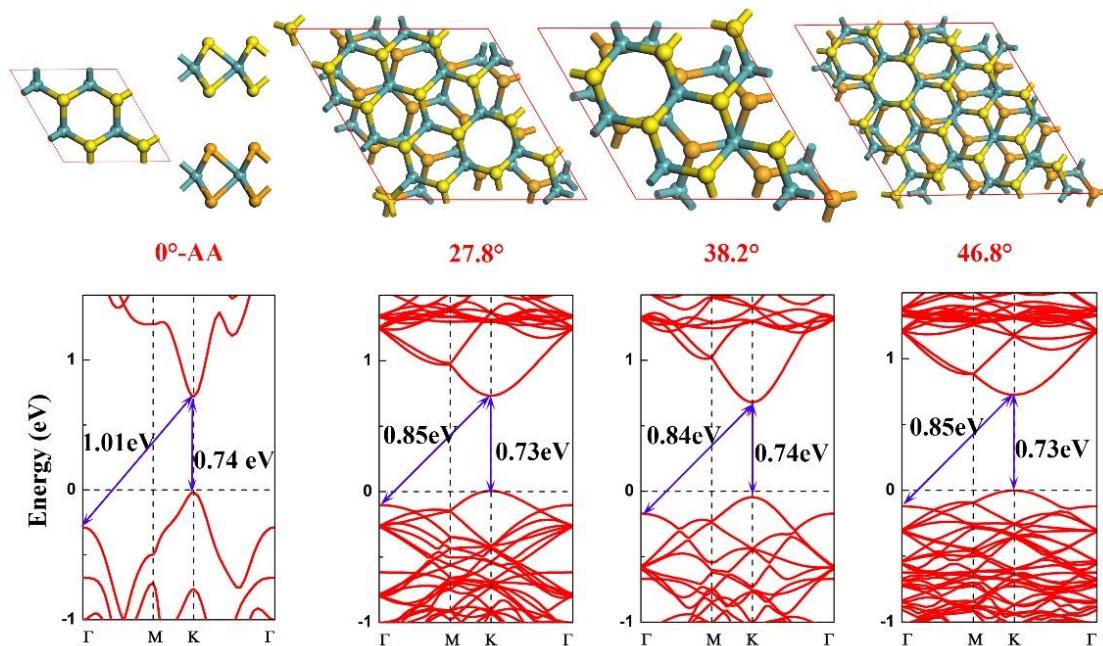


Figure S2. Atomic structures and band structures of the twisted heterobilayer MoS₂/MoSe₂ with the AA stacking order as the initial configuration. The electronic properties versus the rotation angle are almost identical to those of the corresponding MoS₂/MoSe₂ with the T-stacking order as the initial configuration.

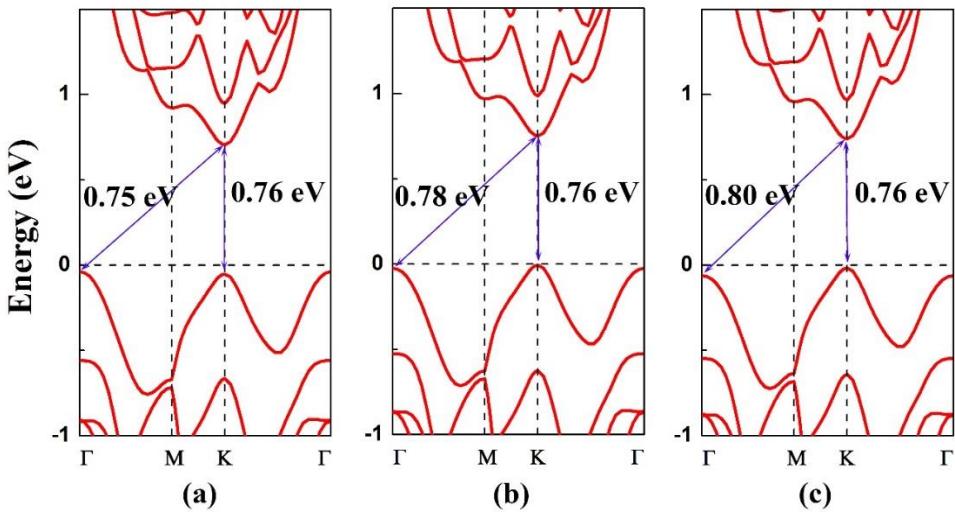


Figure S3. Computed band structures of the C7 stacking for CrSe₂/MoS₂ heterobilayer with enlarging the interlayer distance to (a) 3.3 Å, (b) 3.4 Å and (c) 3.5 Å.

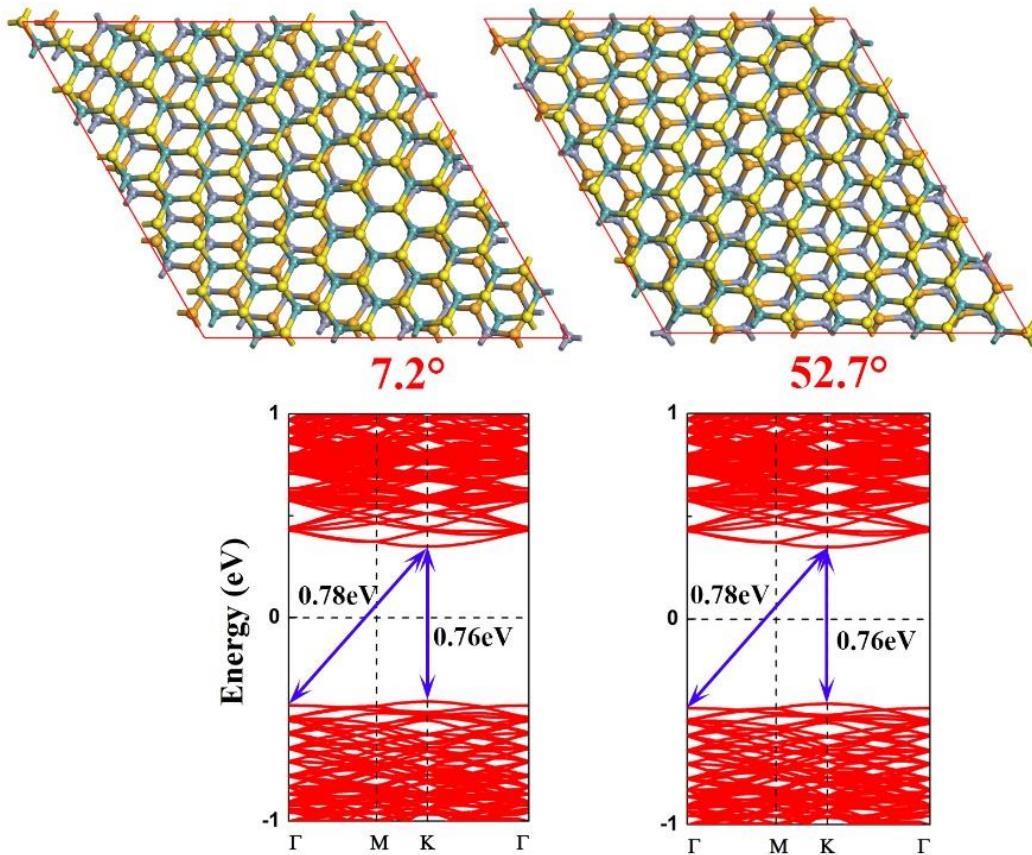


Figure S4. Computed band structures of CrSe₂/MoS₂ heterobilayer with rotation angle of 7.2 ° and 52.7 °. The interlayer distance is 3.40 Å for both 7.2 ° and 52.7 °.

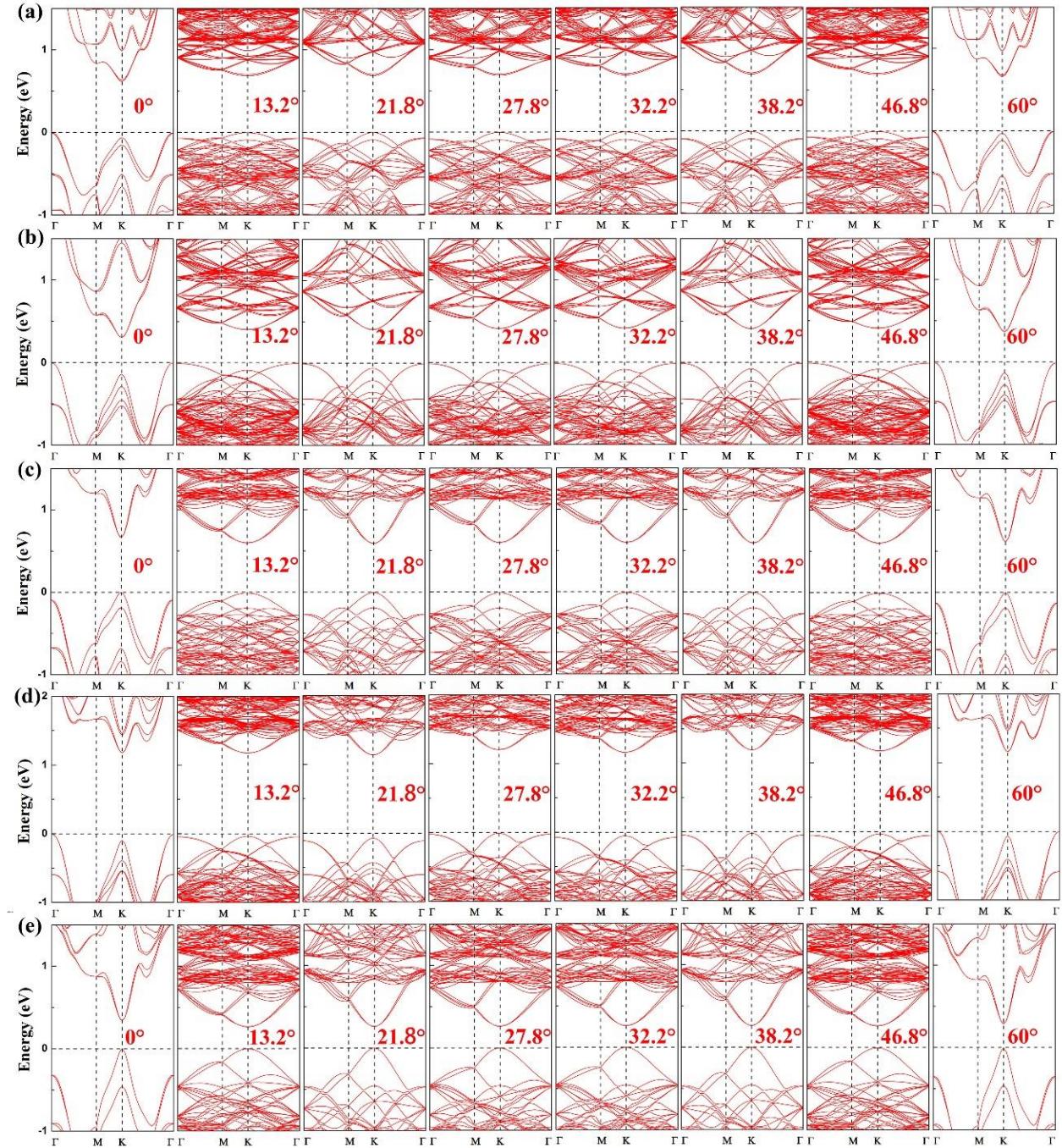


Figure S5. Computed band structures (PBE+SOC) of the heterobilayers of (a) CrSe₂/MoS₂, (b) CrS₂/MoS₂, (c) MoSe₂/MoS₂, (d) WS₂/MoS₂, and (e) WSe₂/MoS₂.